

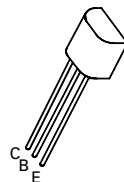
NPN SILICON PLANAR SMALL SIGNAL TRANSISTOR

ZTX341

ISSUE 2 – MARCH 94

FEATURES

- * High voltage
- * Low current



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	100	mA
Base Current	I_B	20	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	300	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +175	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	100		V	$I_C=10\mu A, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	100		V	$I_C=10mA, I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5		V	$I_E=10\mu A, I_C=0$
Collector Cut-Off Current	I_{CBO}		0.5	μA	$V_{CB}=80V, I_E=0$
Collector-Emitter Cut-Off Current	I_{CER}		0.5 10	μA μA	$V_{CE}=80V, R_{BE}=50K\Omega$ $V_{CE}=80V, R_{BE}=50K\Omega \dagger$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.5	V	$I_C=2mA, I_B=0.1mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.0	V	$I_C=2mA, I_B=0.1mA$
Static Forward Current Transfer Ratio	h_{FE}	30			$I_C=2mA, V_{CE}=1V$
Transition Frequency	f_T	80		MHz	$I_C=5mA, V_{CE}=5V$ $f=60MHz$
Output Capacitance	C_{obo}		10	pF	$V_{CB}=6V, f=1MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

$\dagger T_{amb}=100^{\circ}C$

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TYPICAL CHARACTERISTICS

